



STx6NM60N

N-channel 600 V, 0.85 Ω , 4.6 A MDmesh™ II Power MOSFET
TO-220, TO-220FP, IPAK, DPAK, D²PAK

Features

Type	V _{DSS} (@T _{jmax})	R _{DS(on)} max	I _D
STB6NM60N	650 V	< 0.92 Ω	4.6 A
STD6NM60N	650 V	< 0.92 Ω	4.6 A
STD6NM60N-1	650 V	< 0.92 Ω	4.6 A
STF6NM60N	650 V	< 0.92 Ω	4.6 A ⁽¹⁾
STP6NM60N	650 V	< 0.92 Ω	4.6 A

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

- Switching applications

Description

This series of devices implements second generation MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the STMicroelectronics' strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high-efficiency converters.

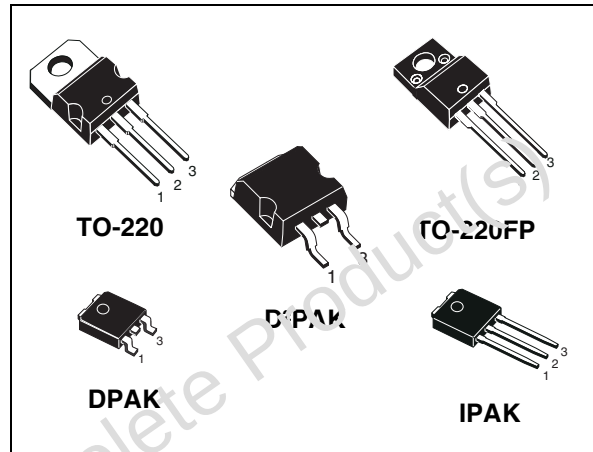
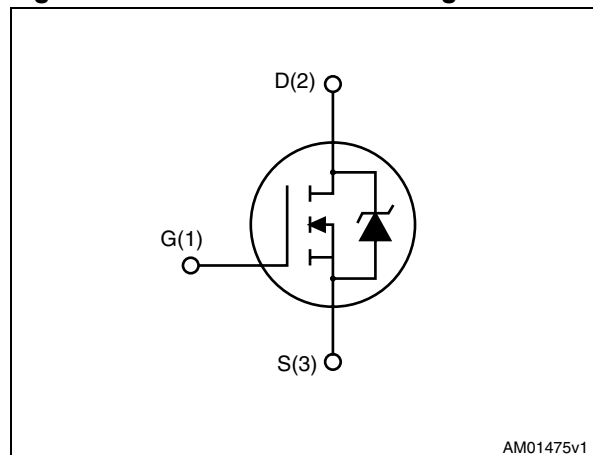


Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB6NM60N	B6NM60N	D ² PAK	Tape and reel
STD6NM60N-1	D6NM60N	IPAK	Tube
STD6NM60N	D6NM60N	DPAK	Tape and reel
STF6NM60N	F6NM60N	TO-220FP	Tube
STP6NM60N	P6NM60N	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, D ² PAK, DPAK, IPAK	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} =0)	600		V
V _{GS}	Gate-source voltage	± 25		V
I _D	Drain current (continuous) at T _C = 25 °C	4.6	4.6 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	2.9	2.9 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	18.4	18.4 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	45	20	W
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)	2500		V
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 150		°C

1. Limited by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 4.6A, di/dt ≤ 400V/μs, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value					Unit
		TO-220	IPAK	DPAK	D ² PAK	TO-220FP	
R _{thj-case}	Thermal resistance junction-case	2.78				5	°C/W
R _{thj-amb}	Thermal resistance junction-amb	62.5	100			62.5	°C/W
T _l	Maximum lead temperature for soldering purpose	300					°C

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	2	A
E _{AS}	Single pulse avalanche energy (starting T _j =25°C, I _D =I _{AS} , V _{DD} = 50 V)	65	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain-source voltage slope	$V_{DD} = 400\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 4.6\text{ A}$	40			V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating @ } 125\text{ }^{\circ}\text{C}$			1 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.3\text{ A}$		0.85	0.92	Ω

1. Characteristics value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$, $I_D = 2.3\text{ A}$		4		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		420 30 4		pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Output equivalent capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to } 480\text{ V}$		70		pF
R_g	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 test signal level = 20 mV open drain		6		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480\text{ V}$, $I_D = 4.6\text{ A}$ $V_{GS} = 10\text{ V}$ Figure 19		13 2 7		nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 2.3\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ Figure 18		10		ns
t_r	Rise time			8		ns
$t_{d(off)}$	Turn-off delay time			40		ns
t_f	Fall time			9		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				4.6	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				18.4	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4.6\text{ A}$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 4.6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$, Figure 20		300		ns
Q_{rr}	Reverse recovery charge			2		μC
I_{RRM}	Reverse recovery current			12		A
t_{rr}	Reverse recovery time	$I_{SD} = 4.6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ Figure 20		470		ns
Q_{rr}	Reverse recovery charge			3		μC
I_{RRM}	Reverse recovery current			12		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

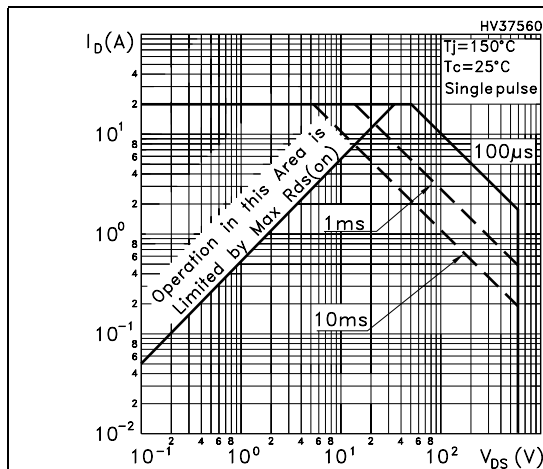


Figure 3. Thermal impedance for TO-220, D²PAK

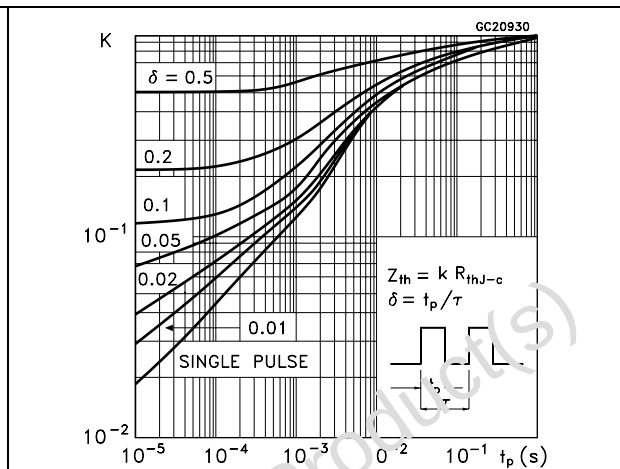


Figure 4. Safe operating area for TO-220FP

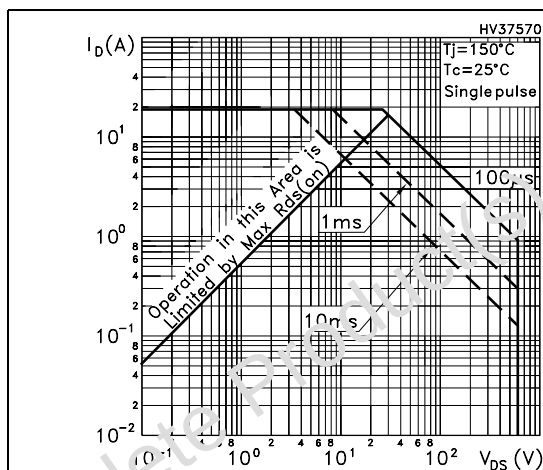


Figure 5. Thermal impedance for TO-220FP

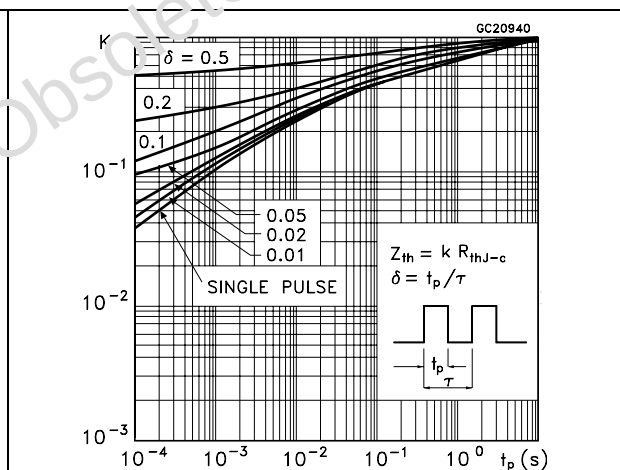


Figure 6. Safe operating area for DPAK, IPAK

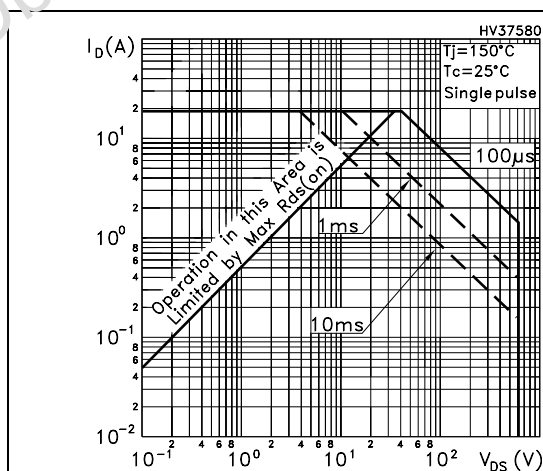


Figure 7. Thermal impedance for DPAK, IPAK

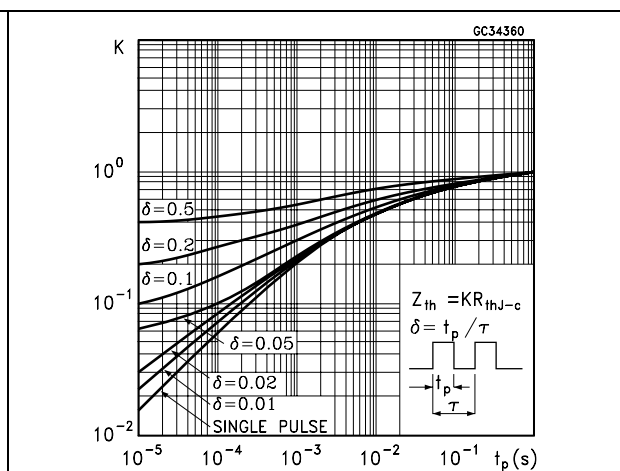


Figure 8. Output characteristics

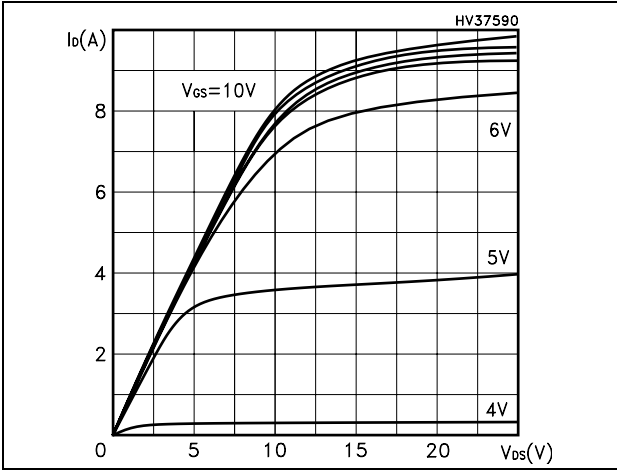


Figure 9. Transfer characteristics

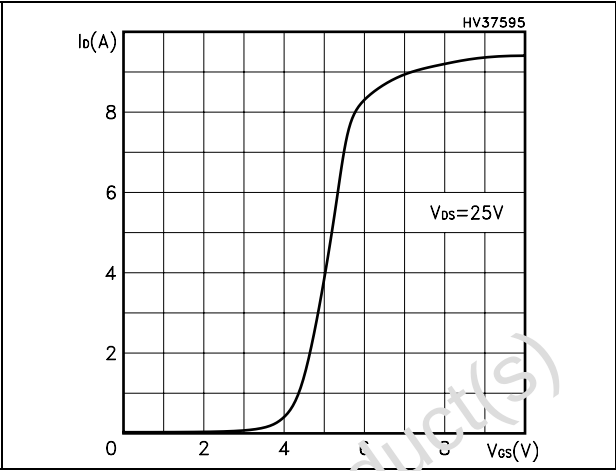


Figure 10. Transconductance

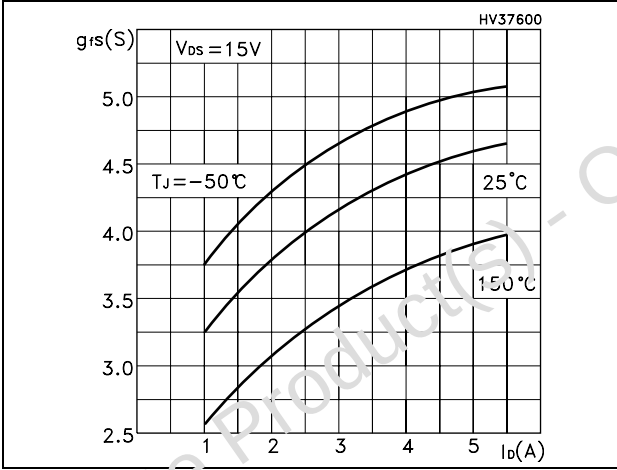


Figure 11. Static drain-source on resistance

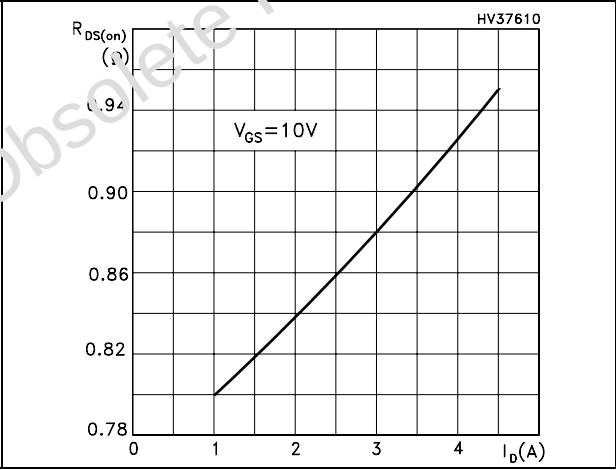


Figure 12. Gate charge vs gate-source voltage

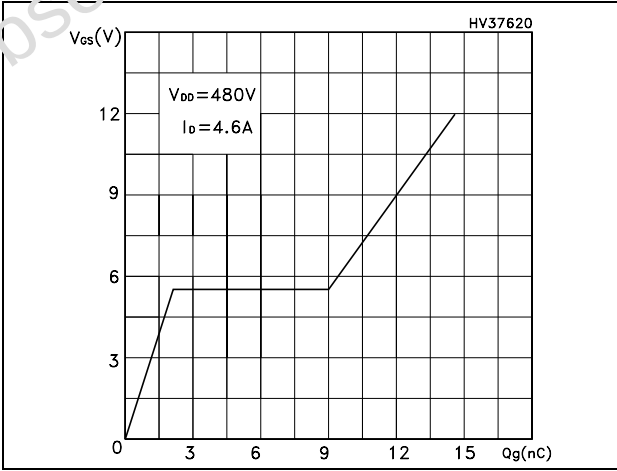


Figure 13. Capacitance variations

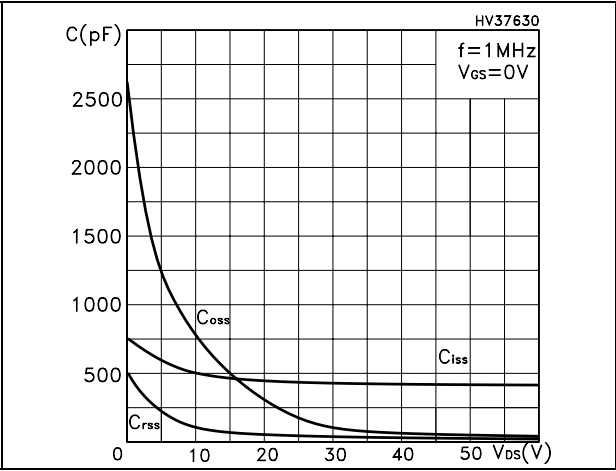


Figure 14. Normalized gate threshold voltage vs temperature

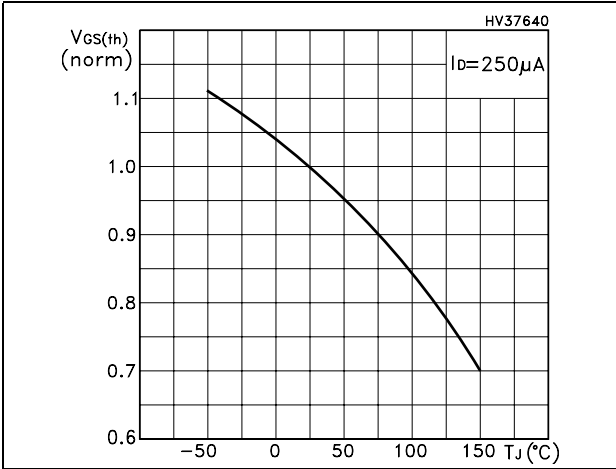


Figure 15. Normalized on resistance vs temperature

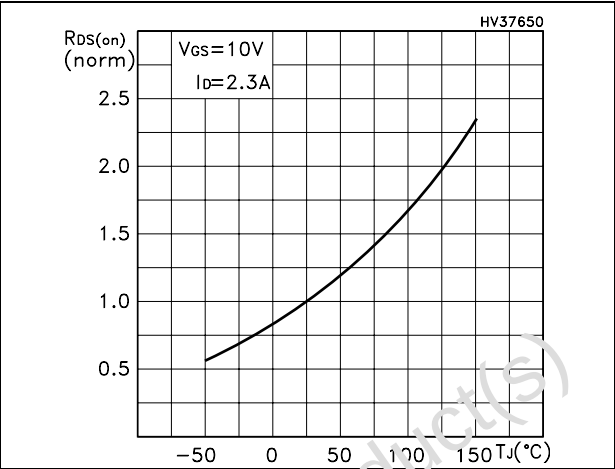


Figure 16. Source-drain diode forward characteristics

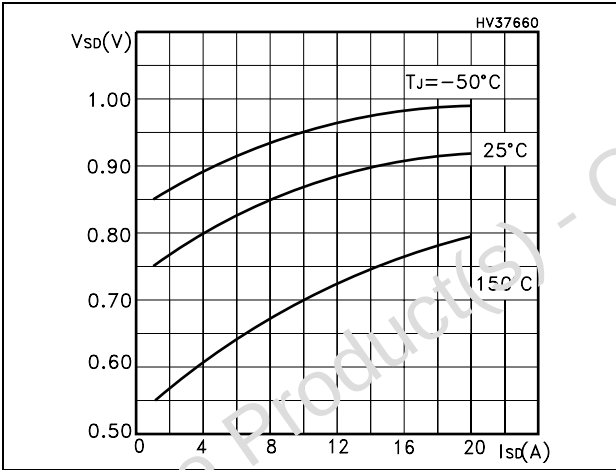
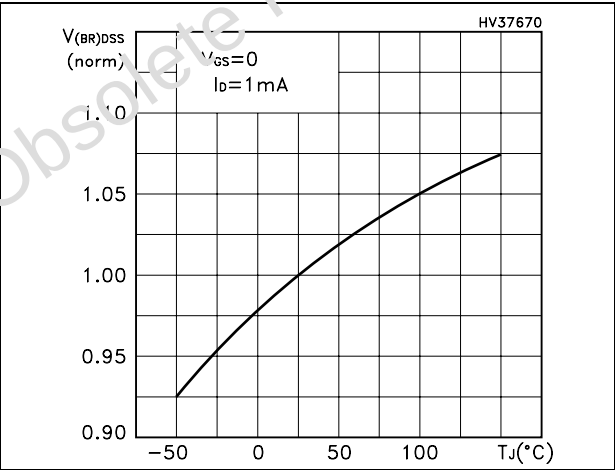


Figure 17. Normalized $B_{V(BR)DSS}$ vs temperature



3 Test circuit

Figure 18. Switching times test circuit for resistive load

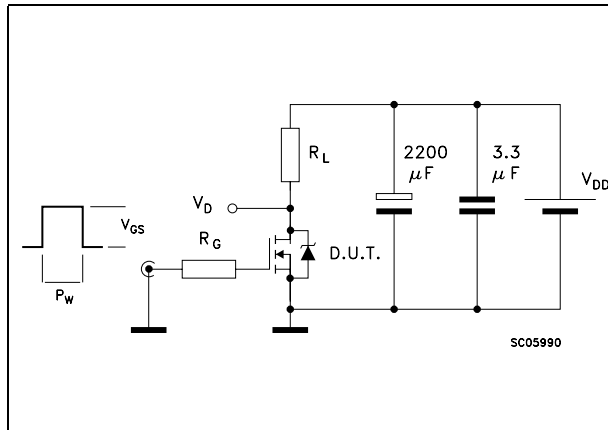


Figure 19. Gate charge test circuit

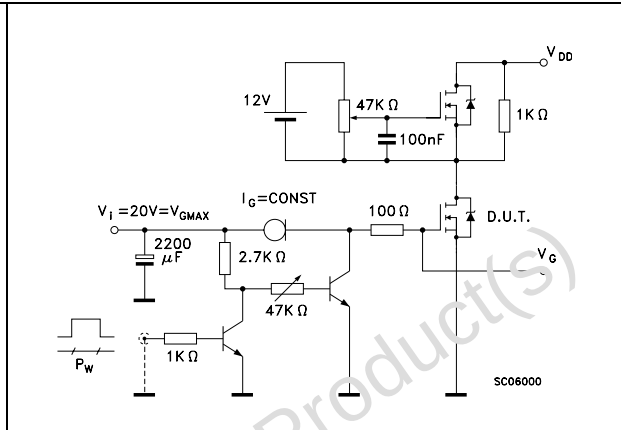


Figure 20. Test circuit for inductive load switching and diode recovery times

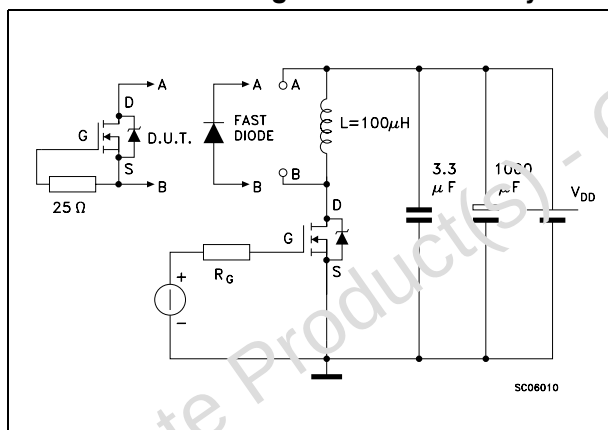


Figure 21. Uncamped inductive load test circuit

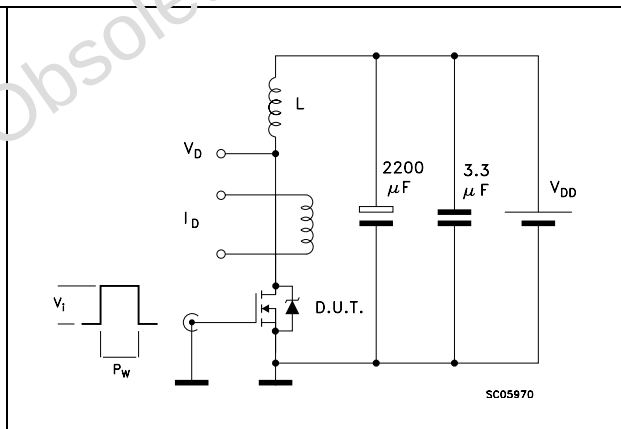


Figure 22. Unclamped inductive waveform

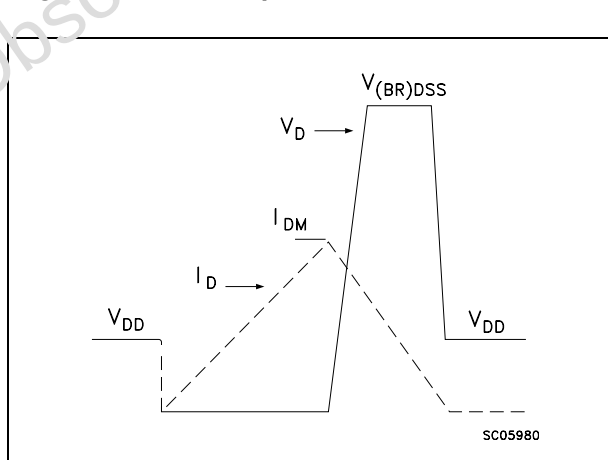
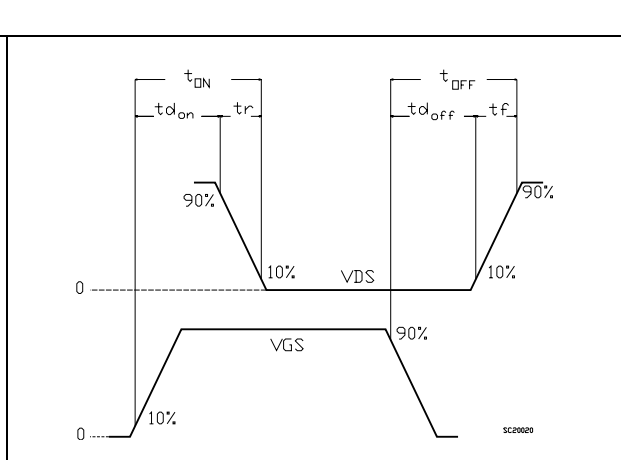


Figure 23. Switching time waveform



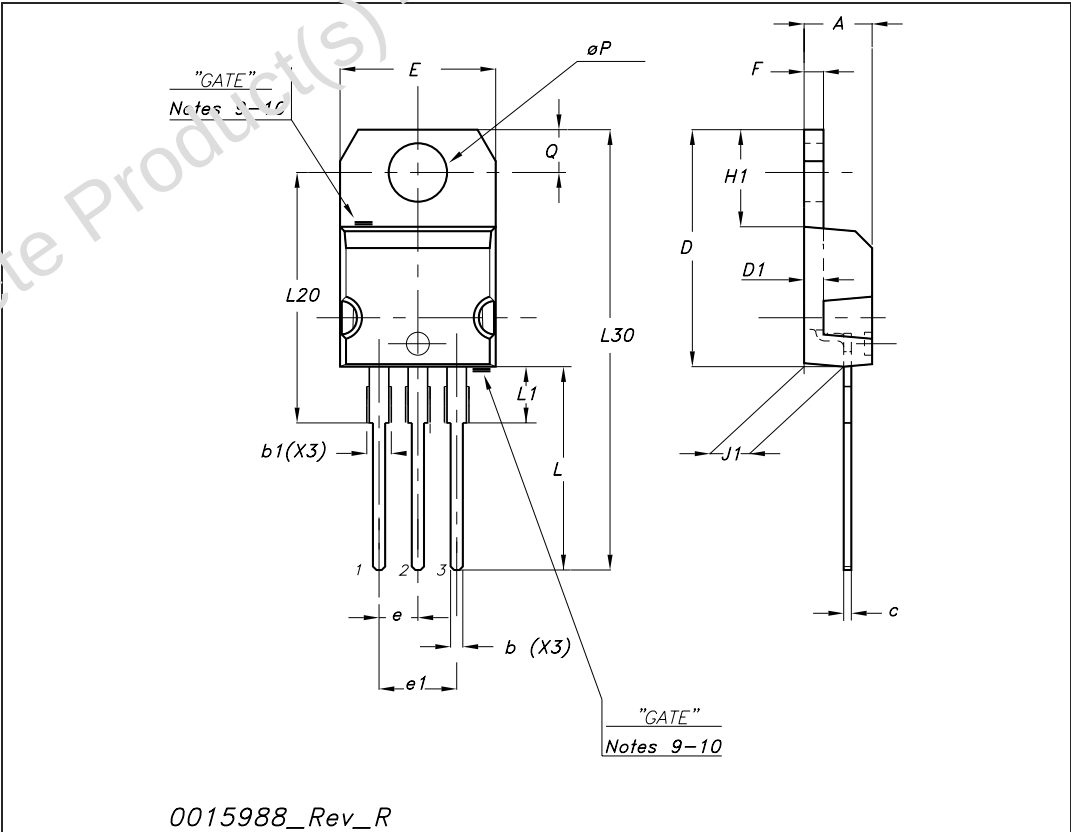
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

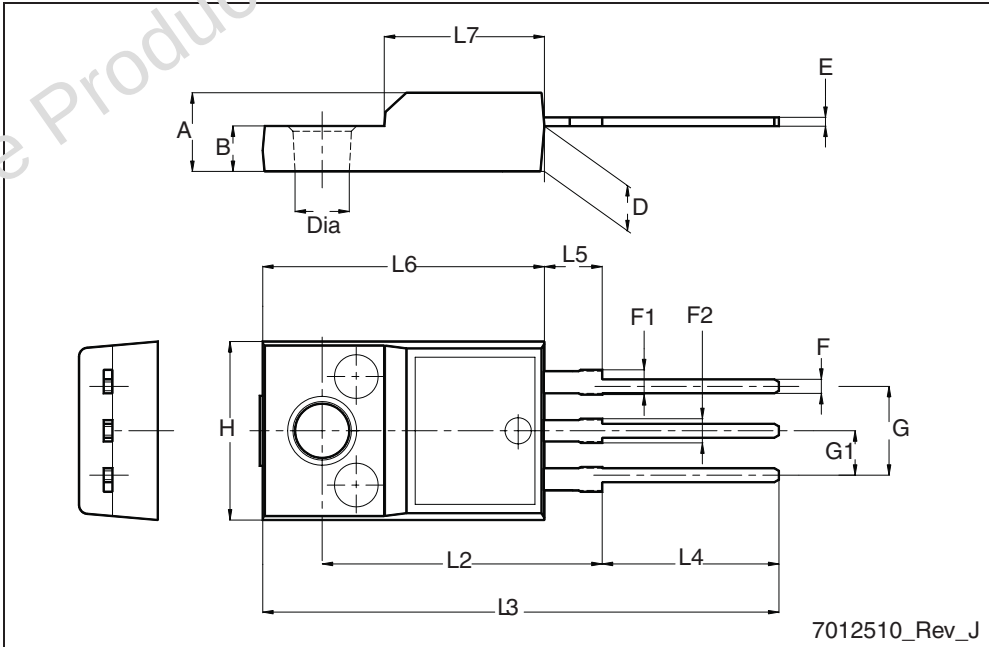
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



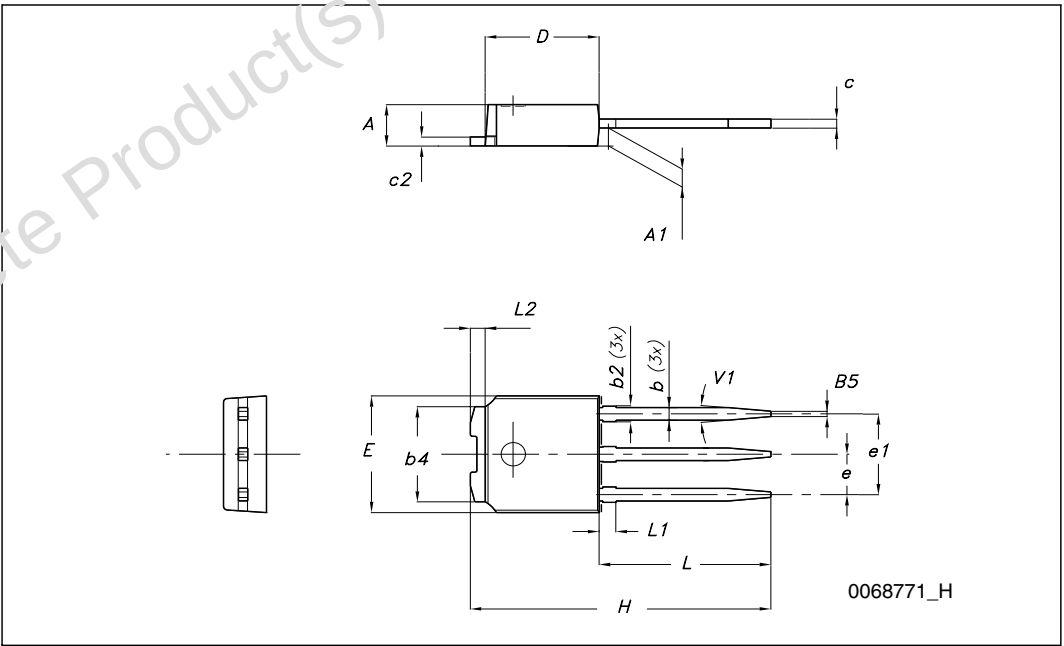
TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



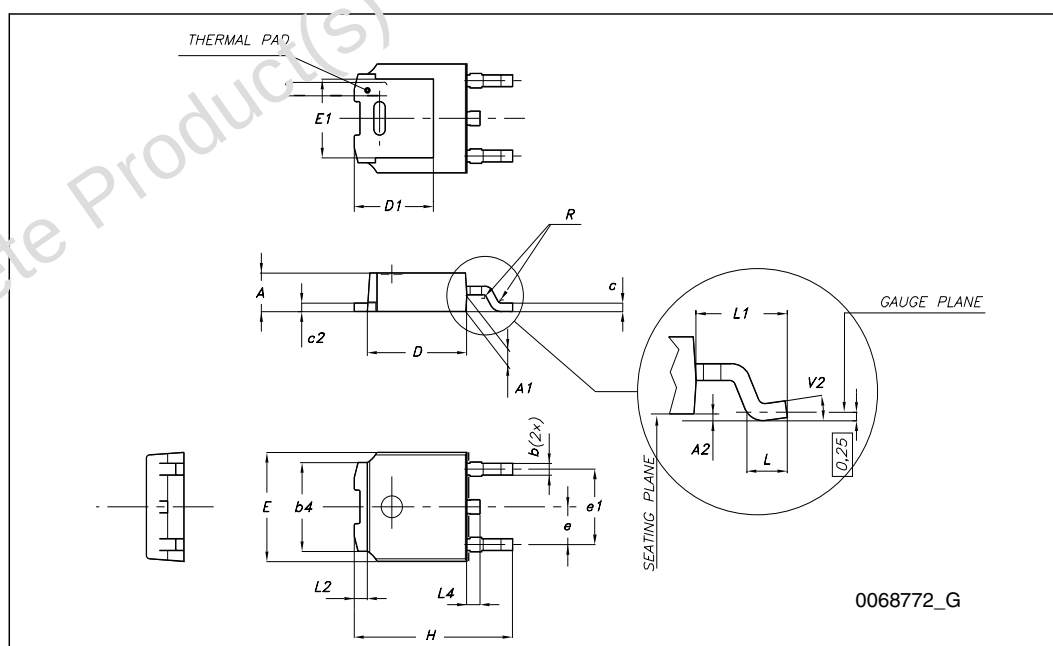
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



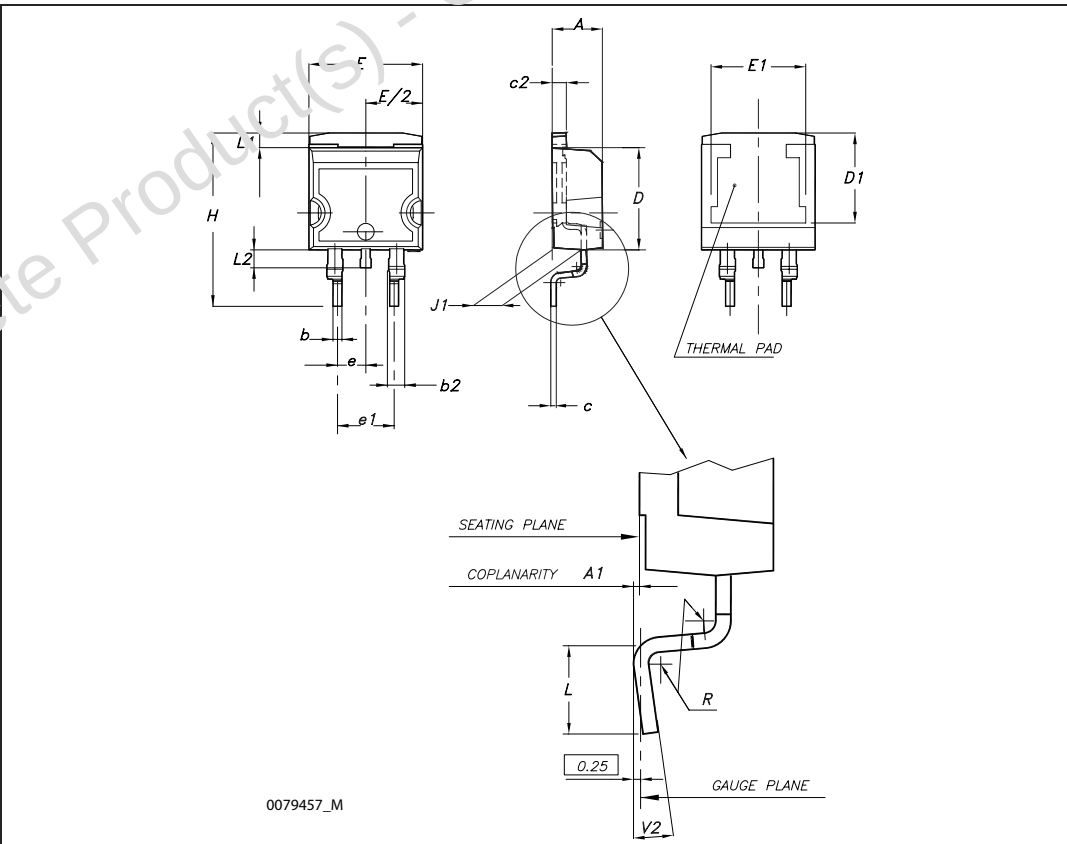
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

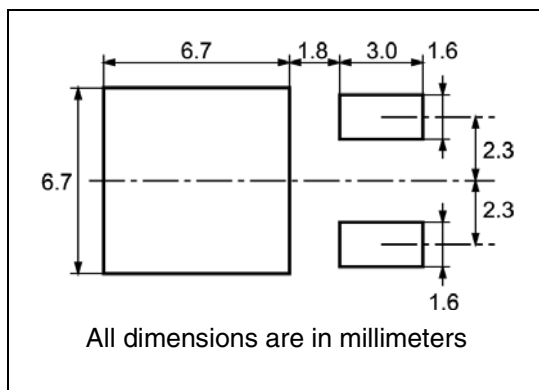


D²PAK (TO-263) mechanical data

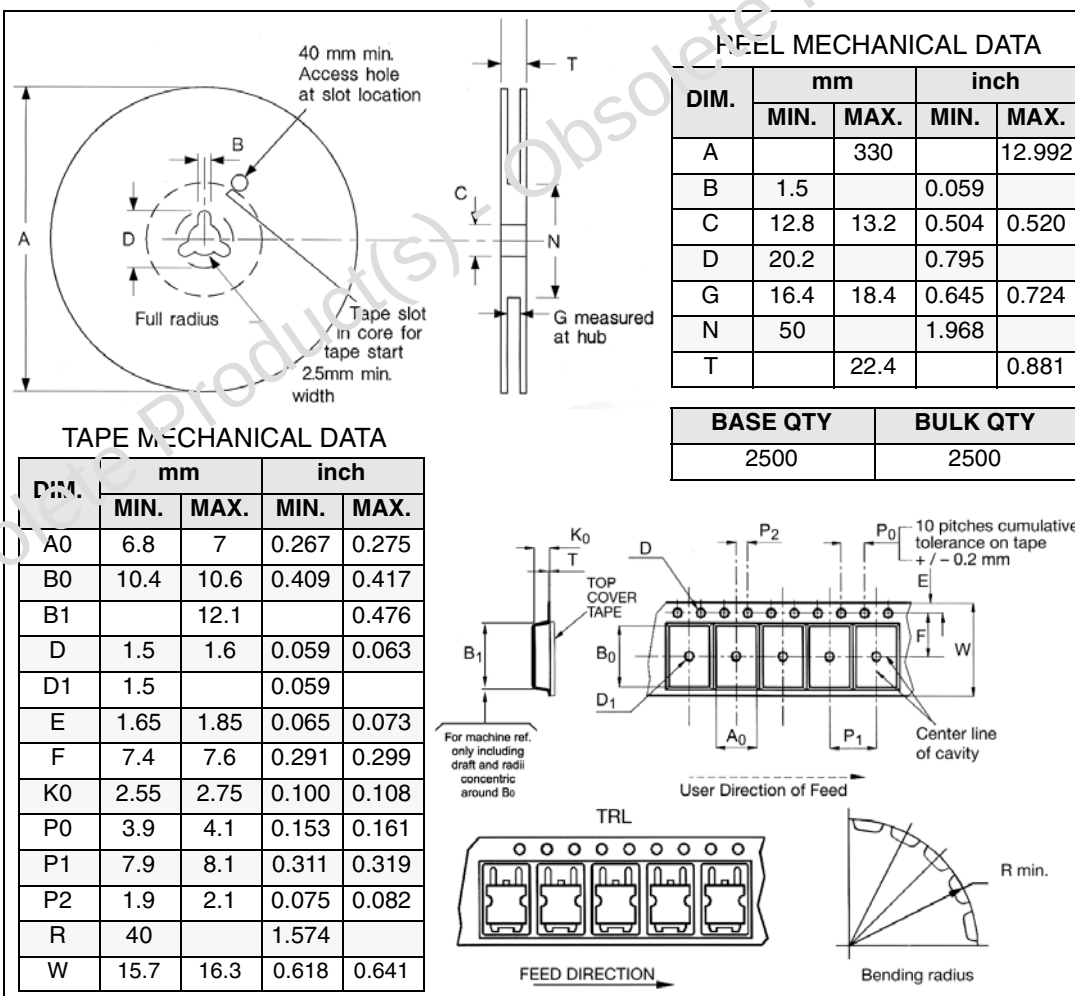
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.098		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

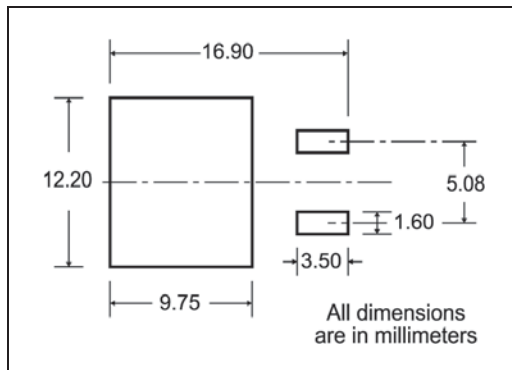


DPAK FOOTPRINT

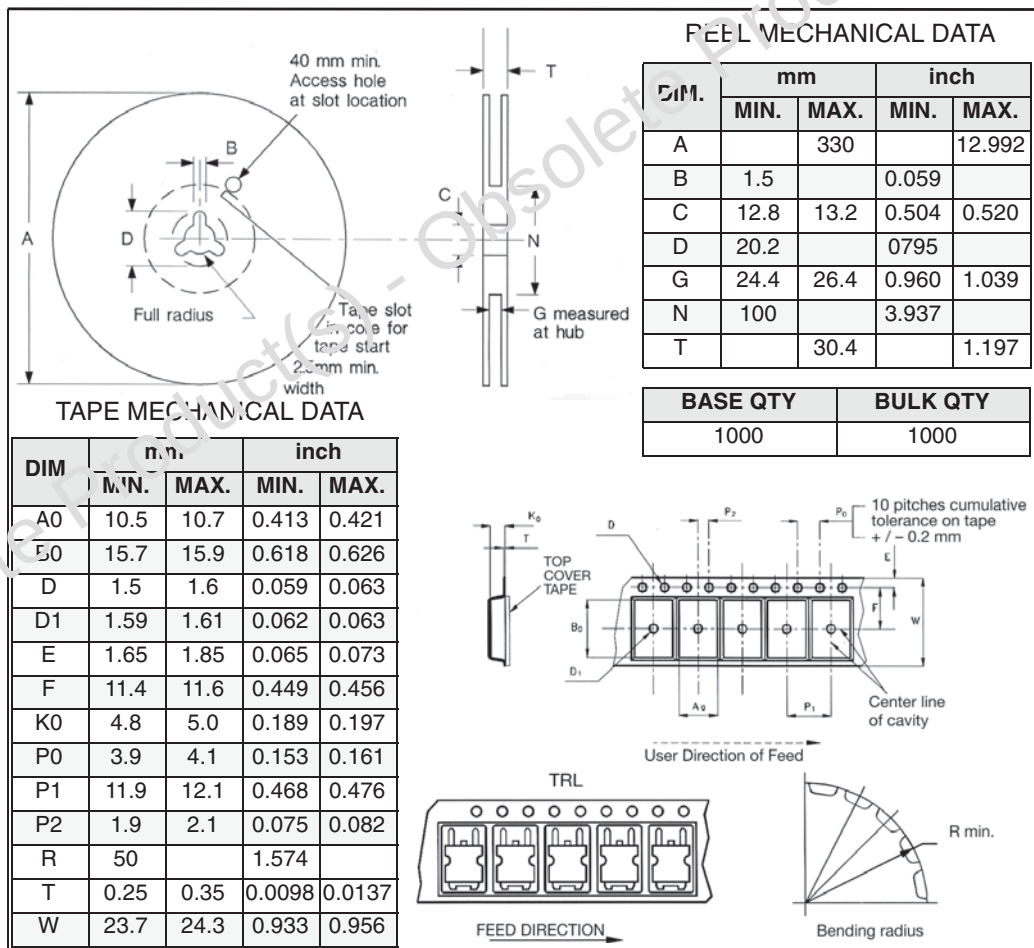


TAPE AND REEL SHIPMENT



D²PAK FOOTPRINT

TAPE AND REEL SHIPMENT



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
09-May-2007	1	First release
01-Jun-2007	2	Corrected value on Table 8: Source drain diode
21-Jan-2009	3	Added new package, mechanical data D ² PAK

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